

2SC2591, 2SC2592

Silicon NPN Epitaxial Planar Type

AF Driver, High Power Amplifier
Complementary Pair with 2SA1111, 2SA1112

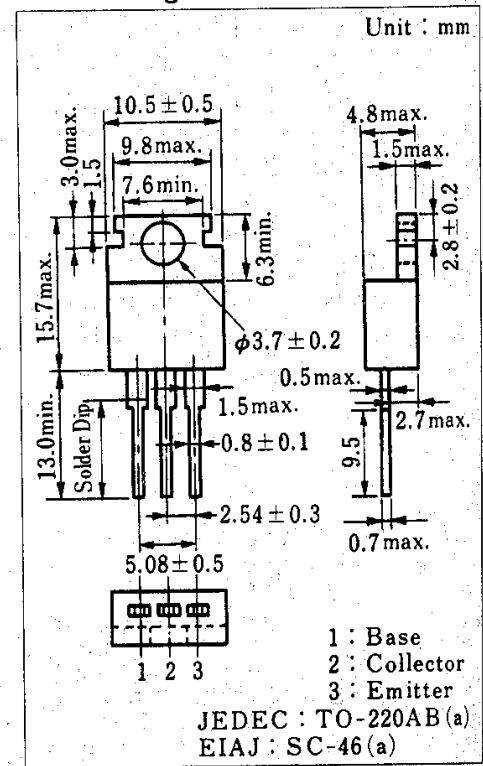
■ Features

- Very good linearity of DC current gain (h_{FE})
- High transition frequency (f_T)
- Optimum for the driver of 60~100W in complementary pair with 2SA1111 and 2SA1112

■ Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	2SC2591	150	V
	2SC2592	180	
Collector-emitter voltage	2SC2591	150	V
	2SC2592	180	
Emitter-base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	1.5	A
Collector current	I_C	1	A
Collector power dissipation ($T_c=25^\circ\text{C}$)	P_C	20	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

■ Package Dimensions



■ Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector-base voltage	2SC2591	$I_C=100 \mu\text{A}, I_B=0$	150			V
	2SC2592		180			
Emitter-base voltage	V_{EBO}	$I_E=10 \mu\text{A}, I_C=0$	5			V
DC current gain	h_{FE1}^*	$V_{CE}=10 \text{V}, I_C=150 \text{mA}$	90	160	330	
	h_{FE2}	$V_{CE}=5 \text{V}, I_C=500 \text{mA}$	50	100		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500 \text{mA}, I_B=50 \text{mA}$		0.5	2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500 \text{mA}, I_B=50 \text{mA}$		1	2	V
Transition frequency	f_T	$V_{CB}=10 \text{V}, I_E=-50 \text{mA}, f=200 \text{MHz}$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10 \text{V}, I_E=0, f=1 \text{MHz}$		20	30	pF

* h_{FE1} Classifications

Class	Q	R	S
h_{FE1}	90 ~ 155	130 ~ 220	185 ~ 330